

Pablo O Vaccaro

List of Publications by Year in descending order

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116
papers

1,293
citations

394286

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32
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119
all docs

119
docs citations

119
times ranked

825
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain-driven self-positioning of micromachined structures. Applied Physics Letters, 2001, 78, 2852-2854.	1.5	145
2	Lasing on scar modes in fully chaotic microcavities. Physical Review E, 2003, 67, 015207.	0.8	69
3	An InGaAs-GaAs vertical-cavity surface-emitting laser grown on GaAs(311)A substrate having low threshold and stable polarization. IEEE Photonics Technology Letters, 1996, 8, 737-739.	1.3	67
4	Plasma mechanism of terahertz photomixing in high-electron mobility transistor under interband photoexcitation. Journal of Applied Physics, 2002, 92, 5756-5760.	1.1	60
5	Selective Optical Generation of Coherent Acoustic Nanocavity Modes. Physical Review Letters, 2007, 98, 265501.	2.9	56
6	Optical actuation of micromirrors fabricated by the micro-origami technique. Applied Physics Letters, 2003, 83, 3647-3649.	1.5	49
7	Blue Laser Diodes Fabricated on m -Plane GaN Substrates. Applied Physics Express, 2008, 1, 011104.	1.1	48
8	Photoluminescence of GaAs/AlGaAs micro-tubes containing uniaxially strained quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 313-316.	1.3	35
9	Morphological dependence of lasing modes in two-dimensional quasi-stadium laser diodes. Journal of the Optical Society of America B: Optical Physics, 2004, 21, 935.	0.9	35
10	Valley-fold and mountain-fold in the micro-origami technique. Microelectronics Journal, 2003, 34, 447-449.	1.1	34
11	Quantum-well microtube constructed from a freestanding thin quantum-well layer. Applied Physics Letters, 2003, 83, 1017-1019.	1.5	34
12	A light-emitting device using a lateral junction grown by molecular beam epitaxy on GaAs (311)A-oriented substrates. Applied Physics Letters, 1998, 72, 818-820.	1.5	33
13	Self-Assembly of Microstage Using Micro-Origami Technique on GaAs. Japanese Journal of Applied Physics, 2003, 42, 4079-4083.	0.8	27
14	Ring and axis mode lasing in quasi-stadium laser diodes with concentric end mirrors. Optics Letters, 2002, 27, 1430.	1.7	26
15	Quantum-Confined Stark Shift Due to Piezoelectric Effect in InGaAs/GaAs Quantum Wells Grown on (111)A GaAs. Japanese Journal of Applied Physics, 1995, 34, 1362-1366.	0.8	25
16	Probing residual strain in InGaAs/GaAs micro-origami tubes by micro-Raman spectroscopy. Journal of Applied Physics, 2006, 99, 063512.	1.1	23
17	Growth and Characterization of Vertical-Cavity Surface-Emitting Lasers Grown on (311)A-Oriented GaAs Substrates by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1996, 35, 6102-6107.	0.8	22
18	Lateral-junction vertical-cavity surface-emitting laser grown by molecular-beam epitaxy on a GaAs (311) A-oriented substrate. Applied Physics Letters, 1999, 74, 3854-3856.	1.5	22

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19	Highly reliable 500 mW laser diodes with epitaxially grown AlON coating for high-density optical storage. Applied Physics Letters, 2009, 95, .	1.5	22
20	Arsenic vapor pressure dependence of surface morphology and silicon doping in molecular beam epitaxial grown GaAs (n 11)A (n =1â€“4) substrates. Microelectronics Journal, 1999, 30, 471-476.	1.1	21
21	Characterization of GaAs-based micro-origami mirrors by optical actuation. Microelectronic Engineering, 2004, 73-74, 429-434.	1.1	21
22	Optical properties of a nanostructure spontaneously formed on GaAs (311)A-oriented substrates. Journal Physics D: Applied Physics, 1996, 29, 2221-2228.	1.3	18
23	Spontaneous Formation of Nanostructures inInxGa1-xAsEpilayers Grown by Molecular Beam Epitaxy on GaAs Non-(100)-oriented Substrates. Japanese Journal of Applied Physics, 1997, 36, 1948-1954.	0.8	17
24	Optoelectronic devices based on lateral p-n junctions fabricated by molecular-beam epitaxy growth of silicon-doped GaAs on patterned (311)A-oriented substrates. IEEE Journal of Quantum Electronics, 2000, 36, 849-857.	1.0	17
25	SiGe/Si microtubes fabricated on a silicon-on-insulator substrate. Journal Physics D: Applied Physics, 2003, 36, L67-L69.	1.3	16
26	Uniaxial-strain-induced transition from type-II to type-I band configuration of quantum well microtubes. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 732-736.	1.3	16
27	Growth by molecularâ€“beam epitaxy and photoluminescence of InGaAs/GaAs quantum wells on GaAs (111)A substrates. Journal of Applied Physics, 1994, 76, 8037-8041.	1.1	15
28	Influence of the Piezoelectric Effect on the Energy Levels of InGaAs/GaAs Strained Quantum Wells Grown on (311)A GaAs. Japanese Journal of Applied Physics, 1995, 34, L13-L16.	0.8	15
29	Oxide-confinement vertical-cavity surface-emitting lasers grown on GaAs(311)A substrates with dynamically stable polarisation. Electronics Letters, 1998, 34, 276.	0.5	14
30	Array of Micromachined Components Fabricated Using â€œMicro-Origamiâ€•Method. Japanese Journal of Applied Physics, 2003, 42, 4024-4026.	0.8	14
31	Quasi-stadium laser diodes with an unstable resonator condition. Optics Letters, 2003, 28, 408.	1.7	12
32	Photoconductivity in stannic oxide films prepared by spray pyrolysis. Journal of Materials Science Letters, 1990, 9, 389-390.	0.5	11
33	Self-assembling GaAs mirror with electrostatic actuation using micro-origami. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 24, 78-81.	1.3	11
34	Characterization of InGaAs/GaAs strainedâ€“layer quantum wells grown on (311)A GaAs substrates. Applied Physics Letters, 1995, 66, 93-95.	1.5	10
35	AlAs oxidation process in GaAs/AlGaAs/AlAs heterostructures grown by molecular beam epitaxy on GaAs (n 11)A substrates. Microelectronics Journal, 1999, 30, 387-391.	1.1	10
36	Possibility of a quasi-liquid layer of As on GaAs substrate grown by MBE as observed by enhancement of Ga desorption at high As pressure. Applied Surface Science, 2000, 159-160, 301-307.	3.1	10

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37	Piezoelectric semiconductor acoustic cavities. <i>Physical Review B</i> , 2005, 72, .	1.1	10
38	Carrier Dynamics in Piezoelectric Quantum Wells Grown on GaAs (111)A, (211)A and (311)A Studied by Time-Resolved Photoluminescence Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1996, 35, 1292-1298.	0.8	9
39	High-frequency performance of lateral p-n junction photodiodes. <i>IEEE Journal of Quantum Electronics</i> , 2001, 37, 830-836.	1.0	9
40	Interdiffusion of Indium in piezoelectric InGaAs \cdot GaAs quantum wells grown by molecular beam epitaxy on (11n) substrates. <i>Journal of Applied Physics</i> , 2004, 96, 3702-3708.	1.1	9
41	Fabrication and current-drive of SiGe \cdot Si $\hat{\sim}$ Micro-origami $\hat{\sim}$ ™ epitaxial MEMS device on SOI substrate. <i>Electronics Letters</i> , 2004, 40, 1333.	0.5	9
42	Thermal transport in epitaxial Si _{1-x} Ge _x alloy nanowires with varying composition and morphology. <i>Nanotechnology</i> , 2017, 28, 505704.	1.3	9
43	AlGaAs/GaAs and InGaAs/GaAs quantum wells grown on GaAs (111)A substrates. <i>Microelectronics Journal</i> , 1996, 27, 411-421.	1.1	8
44	Electroluminescence in Undoped GaAs/AlAs Superlattice due to Avalanche Breakdown. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2577-2579.	0.8	8
45	InAs quantum dots on GaAs substrates with InGaAs strain reducing layer for long wavelength emission. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1193-1196.	0.8	8
46	Effect of material anisotropy on the self-positioning of nanostructures. <i>Nanotechnology</i> , 2006, 17, 1128-1133.	1.3	8
47	Acoustic phonon Raman scattering induced by a built-in electric field. <i>Physical Review B</i> , 2008, 77, .	1.1	7
48	Time resolved magneto-optical spectroscopy on InGaAs nanostructures grown on (311)A and (100)-oriented substrates. <i>Applied Physics Letters</i> , 1999, 74, 676-678.	1.5	6
49	Optical transitions of Al _{0.35} Ga _{0.65} As/GaAs asymmetric double quantum wells grown on GaAs(n 11)A (n $\hat{\sim}$ 4) substrates. <i>Microelectronics Journal</i> , 1999, 30, 433-437.	1.1	6
50	Nonradiative centers in InAs quantum dots revealed by two-wavelength excited photoluminescence. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 849-852.	1.3	6
51	Composition and Strain Imaging of Epitaxial In-Plane SiGe Alloy Nanowires by Micro-Raman Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2015, 119, 22154-22163.	1.5	6
52	Effects of CdCl ₂ on the growth of CdTe on CdS films for solar cells by isothermal close-spaced vapour transport. <i>Journal Physics D: Applied Physics</i> , 1991, 24, 1886-1889.	1.3	5
53	Atomic-Layer Control in GaP Growth by Laser-Triggered Chemical Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1993, 32, L335-L337.	0.8	5
54	Nano-oxidation of Vanadium Thin Films using Atomic Force Microscopy. <i>Journal of Materials Science Letters</i> , 1998, 17, 1941-1943.	0.5	5

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55	MBE growth of AlGaAs/GaAs double- heterostructure light emitting diodes on GaAs(111)A and (211)A substrates using all-silicon doping. Microelectronics Journal, 1997, 28, 1019-1023.	1.1	4
56	Lateral wet oxidation of AlAs layer in GaAs/AlAs heterostructures grown by MBE on GaAs (n11)A substrates. Journal of Crystal Growth, 1999, 198-199, 1136-1140.	0.7	4
57	MBE growth of AlGaAs/GaAs heterostructure and silicon doping on GaAs(n11)A (n=1-4) substrates. Journal of Crystal Growth, 1999, 201-202, 226-231.	0.7	4
58	Performance analysis of lateral p-n junction laser-transistor. Journal of Applied Physics, 2002, 92, 4459-4464.	1.1	4
59	Electric Field Induced Carrier Sweep-Out in Tandem InGaN Multi-Quantum-Well Self-Pulsating Laser Diodes. Japanese Journal of Applied Physics, 2011, 50, 020209.	0.8	4
60	Growth and Characterization of Epitaxial In-plane SiGe Alloy Nanowires. Materials Today: Proceedings, 2015, 2, 548-556.	0.9	4
61	In-situ RHEED observation on surface reactions in laser-triggered chemical beam epitaxy of GaP. Applied Surface Science, 1994, 79-80, 227-231.	3.1	3
62	Rapid collapse of Wannier-Stark localization caused by space charge electric field screening in short-period superlattices. Journal of Applied Physics, 1996, 80, 5094-5105.	1.1	3
63	Intersubband electroluminescence using X-ray carrier injection in a GaAs/AlAs superlattice. Applied Physics Letters, 2000, 77, 848-850.	1.5	3
64	Photoluminescence property of uniaxial strained GaAs/AlGaAs quantum wells contained in a micro-tube. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 391-392.	1.3	3
65	Lasing characteristics and modal gain of a lateral-junction InGaAs/GaAs edge-emitting laser diode grown on a patterned GaAs (311) A-oriented substrate. Applied Physics Letters, 2003, 82, 2951-2953.	1.5	3
66	Physics and characteristics of a lateral p-n junction tunneling transistor. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 867-871.	1.3	3
67	Self-assembled GaAs micromirrors monolithically integrated with LEDs. , 2005, , .		3
68	Localized thinning for strain concentration in suspended germanium membranes and optical method for precise thickness measurement. AIP Advances, 2018, 8, 115131.	0.6	3
69	Reflection high-energy electron diffraction observation of surface reaction triggered by pulsed laser irradiation during GaP growth in chemical beam epitaxy. Applied Physics Letters, 1993, 63, 2097-2099.	1.5	2
70	Strain relaxation in InGaAs/GaAs quantum wells grown on GaAs (111)A substrates. Journal of Crystal Growth, 1995, 150, 503-507.	0.7	2
71	The growth of (InGa)As quantum wells on GaAs(111)A, (211)A and (311)A substrates. Microelectronics Journal, 1997, 28, 1011-1018.	1.1	2
72	MBE growth of lattice-matched and mismatched films on non-(001) GaAs substrates. Thin Solid Films, 1997, 306, 192-197.	0.8	2

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73	Optical properties of self-assembled InAs quantum dots grown on GaAs(211)A substrate. Thin Solid Films, 2000, 380, 97-100.	0.8	2
74	Steady-state characteristics of lateral p-n junction vertical-cavity surface-emitting lasers. Journal of Applied Physics, 2001, 90, 2654-2659.	1.1	2
75	On the design and fabrication precision of Micro-Origami devices. , 0, , .		2
76	Lateral p-n junctions for high-density LED arrays. Microelectronics Journal, 2003, 34, 355-357.	1.1	2
77	Inter-dot electron transport in coupled InAs quantum dots under a magnetic field. Semiconductor Science and Technology, 2004, 19, S54-S55.	1.0	2
78	Optimization of InAs quantum dots formation on (311)A substrate. Journal of Crystal Growth, 2005, 275, e2257-e2261.	0.7	2
79	Electron drift reversal caused by remaining holes in semiconductor superlattices due to effective-mass filtering. Physical Review B, 1996, 53, R13283-R13286.	1.1	1
80	Piezoelectricity and carrier dynamics in In _{0.2} Ga _{0.8} As/GaAs single quantum wells grown on (n11)A-oriented GaAs (n=1, 2, 3). Microelectronics Journal, 1997, 28, 749-755.	1.1	1
81	Lateral-junction light emitting devices grown by molecular beam epitaxy on GaAs (311)A-oriented substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 94-98.	1.7	1
82	Population inversion between subbands in simple periodical GaAs/AlAs superlattices. IEE Proceedings: Optoelectronics, 2000, 147, 225-228.	0.8	1
83	Local degradation of selectively oxidized AlGaAs/AlAs distributed Bragg reflectors in lateral-injection vertical-cavity surface-emitting lasers. Applied Physics Letters, 2000, 77, 3905-3907.	1.5	1
84	Self-assembly of micro-stage using micro-origami technique on GaAs. , 0, , .		1
85	Photoluminescence from High Γ -Electron Subbands and Intersubband Electroluminescence Using χ Carrier Injection in a Simple GaAs/AlAs Superlattice. Japanese Journal of Applied Physics, 2002, 41, 5073-5077.	0.8	1
86	Pressure dependence of the electronic structure of a [311] piezoelectric χ carrier injection in a simple GaAs/AlAs superlattice. Physical Review B, 2010, 82, .	1.1	1
87	Spectroscopic imaging ellipsometry of self-assembled SiGe/Si nanostructures. Applied Surface Science, 2017, 421, 547-552.	3.1	1
88	Isothermal close-spaced vapour growth of CdTe for CdS/CdTe solar cells. Journal of Materials Science Letters, 1991, 10, 47-48.	0.5	0
89	Model for reflection high-energy electron diffraction intensity recovery during GaP growth in laser-triggered chemical beam epitaxy. Applied Physics Letters, 1993, 63, 3601-3603.	1.5	0
90	High performance strained-layer InGaAs quantum well lasers grown on a (311)A GaAs substrate. , 0, , .		0

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91	In-situ reflection high-energy electron diffraction observation of laser-triggered GaP growth in chemical beam epitaxy. Journal of Crystal Growth, 1994, 136, 89-93.	0.7	0
92	Piezoelectric effect in InGaAs/GaAs quantum wells grown on (111)A GaAs observed by photoluminescence spectroscopy. , 0, , .		0
93	Low dimensional carrier confinement structure grown on patterned GaAs(111)A substrates by molecular beam epitaxy. Microelectronic Engineering, 1998, 43-44, 403-407.	1.1	0
94	High-resolution X-ray diffraction study of AlAs/Al _{0.5} Ga _{0.5} As/GaAs quantum well structures grown by molecular beam epitaxy on (111)A GaAs. Journal of Crystal Growth, 2000, 213, 214-220.	0.7	0
95	Epitaxial growth and amphoteric doping on GaAs (111)A-oriented substrates. , 0, , .		0
96	Theoretical analysis of transient processes in lateral p-n junction photodiodes. , 0, , .		0
97	Longitudinal mode behavior of a lateral-junction edge-emitting laser diode. , 0, , .		0
98	Observation of electronic band-structure modification in microtubed quantum well. , 0, , .		0
99	Excitation of plasma oscillations and terahertz photomixing in high-electron mobility transistor. , 2002, , .		0
100	Influence of substrate orientation on self-assembled InAs/GaAs quantum dots for long wavelength emission grown by molecular beam epitaxy. , 0, , .		0
101	Si doped p- and n-type Al _x Ga _{1-x} As epilayers for high density lateral-junction LED arrays on [311]A patterned substrate. , 0, , .		0
102	Device model for three-terminal lateral p-n junction quantum well lasers. , 2003, , .		0
103	Si doped p- and n-type Al _x Ga _{1-x} As epilayers for high density lateral-junction LED arrays on (311)A patterned substrate. Solid-State Electronics, 2004, 48, 1791-1794.	0.8	0
104	Optical and transport studies in coupled InAs quantum dots embedded in GaAs. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 317-321.	1.3	0
105	Lateral junctions for high-density integration of optoelectronic devices. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 324-328.	1.3	0
106	Generation of Ultrasonic Waves from an Optically Driven GaAs Thin Film. , 0, , .		0
107	Novel LEDs using unique lateral p-n junctions on GaAs (311)A patterned substrates. , 2004, 5366, 212.		0
108	High-density light-emitting diodes using a lateral p-n junction on patterned (311)A GaAs substrates. IEICE Electronics Express, 2004, 1, 86-91.	0.3	0

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109	Strain Reduction and Long Wavelength Emission from InAs/GaAs Quantum Dots by Using Growth Interruption in Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2430-2432.	0.8	0
110	Selective optical generation of a coherent acoustic nanocavity mode. AIP Conference Proceedings, 2007, , .	0.3	0
111	Confined optical phonons in piezoelectric [311] GaInAs/AlAs superlattices probed by Raman scattering. Journal of Physics: Conference Series, 2007, 92, 012067.	0.3	0
112	Strain profile of the wall of semiconductor microtubes: A micro-Raman study. Physica Status Solidi (B): Basic Research, 2007, 244, 380-385.	0.7	0
113	Intersubband electroluminescence using X- \hat{I} carrier injection in a GaAs/AlAs double-quantum-well superlattice. Springer Proceedings in Physics, 2001, , 729-730.	0.1	0
114	Electric Field Induced Carrier Sweep-Out in Tandem InGaN Multi-Quantum-Well Self-Pulsating Laser Diodes. Japanese Journal of Applied Physics, 2011, 50, 020209.	0.8	0
115	Laser decomposition of surface adsorbed metalorganics in MOMBE growth of GaP. , 1994, , 163-166.		0
116	Growth of polycrystalline CdIn ₂ S ₄ on US films. Journal of Materials Science Letters, 1993, 12, 553-554.	0.5	0